Abstracts

Pulse-Doped GaAs MESFETs with Planar Self-Aligned Gate for MMIC

S. Nakajima, K. Otobe, N. Kuwata, N. Shiga, K.-I. Matsuzaki and H. Hayashi. "Pulse-Doped GaAs MESFETs with Planar Self-Aligned Gate for MMIC." 1990 MTT-S International Microwave Symposium Digest 90.3 (1990 Vol. III [MWSYM]): 1081-1084.

A pulse-doped GaAs MESFET with n+ self-aligned planar gate has been developed. This device shows excellent drain current linearity and minimum noise figures of 0.72dB (1.15dB) with associated gains Of 10.5dB (8.5dB) at 12GHz (18 GHz), Furthermore, excellent uniformity and reproducible device characteristics also have been realized.

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